



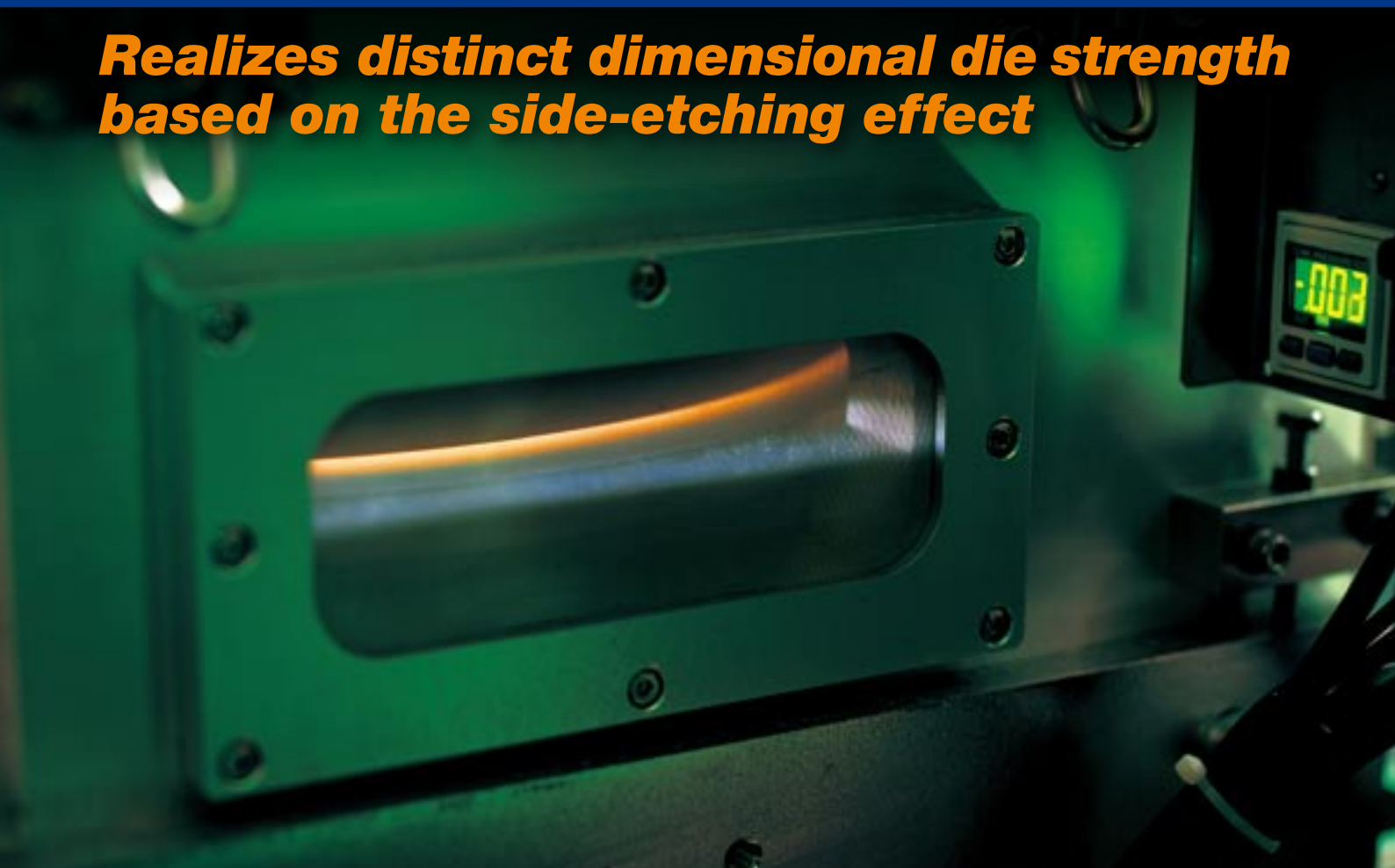
DISCO

Kiru · Kezuru · Migaku Technologies



Fully Automatic Dry Etcher DFE8040/8060

Realizes distinct dimensional die strength based on the side-etching effect



Stress relief using dry etching

The DFE8040/8060 is a stress relief machine that uses dry etching based on fluoride gas plasma. By removing the grinding damage layer from the wafer backside, there is a decline in wafer breakage, improvement in die strength and reduction in warpage. As a result, it improves the production yield in the packaging process. In addition, because it is a complete dry process, chemical penetration or contamination does not occur. Also, since it is a no-load process, dry etching is suitable for fragile devices.

In combination with the DBG process, there is a further die strength improvement

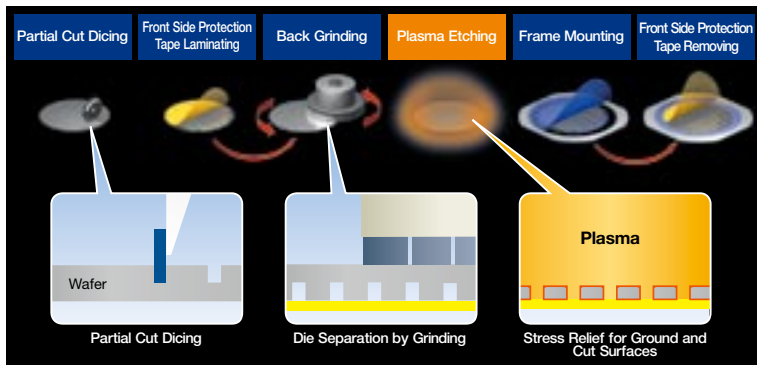
If the DBG process is combined with the dry etching, in addition to removing the grinding damage layer from the wafer backside, removal of the cutting damage from dicing is also achieved due to side-etching effect. Compared to the stress relief of just the wafer backside, DBG processing with dry etching secures greater die strength.



DFE8060

DFG8560





Fully Automatic Dry Etcher DFE8040/8060



Improve product yield with the in-line system

The use of this machine is premised on the in-line specification with the DISCO DFG8560, DFG8540, DGP8760, or DGP8761 grinder. It is also possible to use in-line with the DFM2700 or DFM2800 multifunction wafer mounter.

Able to process rough surfaces to improve the adhesion of backside electrode

By conditioning the process surface before etching, it is possible to roughen the plane roughness while it is clean. As a result of this, adhesion improvement of the metallization layer and reduction of Ohmic resistance* can be expected for backside electrode formation

Safe Design

This dry etcher uses innocuous SF₆ gas. Although harmful gas is produced in a very small quantity, it can be removed via the abatement tower. In the inherently dangerous parts of the machine, interlocks are used to ensure safety. Also, the machine structure conforms to EU machine protocols and EMC protocols.



Before Etching



After Etching

*Ohmic Resistance: Is the sum of the contact resistance between materials and material specific resistance. Reduction of Ohm Resistance is important in the case of power MOS and other devices. The lower the resistance, the more ability there is to control the power loss at the time of device operation. Also, a higher current can pass through the device.

DFE8040/8060 Specifications

	DFE8040	DFE8060
Wafer Diameter	ø8"	ø8" or ø12"
Processing Method	High-density, high-pressure, narrow-gap plasma	
Treatment gas used	SF ₆ /He/N ₂	
Wafer transport section	2	
No. of cassettes	2	
Cassette section wafer flow	Open flow (Storage only)	
Transfer arm	<ul style="list-style-type: none"> Transports wafers from the spinner table of the grinder to the chuck table in the chamber. Transports etched wafers from the chuck table in the chamber to the dummy table. 	
Dummy table	Table onto which etched wafers are transported by the transfer arm before they are unloaded into the cassette by the robot.	
Robot	Transports etched wafers from the dummy table to the cassette.	
Cassette stage	Plate on which a cassette to store etched wafers is placed.	
Cassette used	DBG cassette only	
Utility Unit	Dry-pump Used to exhaust the chamber. *The recommended overhaul interval is 12 months.	
Exhaust velocity	m ³ /h	27
Ultimate pressure	Pa	10 abs
Rotary pump	Used to vacuum the chuck table. *The recommended overhaul interval is 12 months.	
Exhaust velocity	m ³ /h	1.9
Ultimate pressure	Pa	0.3 abs
RF power	High-frequency power used for plasma generation	
Mass flow controller	Regulates supply gas flow.	
Valves	Used for etching section/utility gas section operation control.	
Gas detector	Detects HF leakage from the machine/utility unit. *It is recommended that the break monitor is calibrated once in half a year.	
Coolant Unit	(2: one for cooling the upper electrode and the other for cooling the lower electrode) *The below specifications show the values for one unit.	
Temperature set up range	°C	+5 ~ +35
Max. flow	L/min	15 12
Max. pumping pressure	MPa	0.42
Cooling capacity	kW	2.41 (water temperature set at 20 °C) 3.5 (water temperature set at 20 °C)
Water used	Deionized water	
Utilities	Electricity	
Power supply	200 ~ 240 V AC±10 % 3-phase (50/60 Hz) For other than the above voltages, a transformer is necessary	
Power consumption	kW	5.0 (during plasma generation) 7.0 (during plasma generation) 3.4 (during standby) 4.0 (during standby)
Maximum power	kVA	17 25
Treatment Gas	Gas used SF ₆ : 99.99% or higher in purity, He : 99.99% or higher in purity	
Pressure reducer	Mpa	0.1 Variation: 0.03 at Max. *The pressure regulator and the gas filter should be furnished by the user.
Purge Gas	Gas used N ₂	
Supply pressure	MPa	Range: 0.5 to 0.8, Variation: 0.03
For chamber	Flow rate L/min 50 or higher	
Consumption per wafer	L	6 *Provided that the purge time is 7 sec. and the wafer processing time is 60 sec. per wafer.

	DFE8040	DFE8060
For dry pump	Flow rate L/min 1.5	
Consumption per wafer	L	1.5 *Provided that wafer processing time per wafer is 60 sec.
Air Supply pressure	MPa	Range: 0.5 ~ 0.8, Variation: 0.03 Max.
Flow rate	L/min(ANR)	400 or higher
Water	Water used for cooling electrodes:	
Coolant water (Coolant unit)	L	10 ~ 15 (Total of two coolant units) *Water is circularly used. Supply deionized water as needed.
Air Exhaust	Machine main body exhaust system:	
Function	Detect gas leakage inside the machine. *This system prevents harmful gases from leaking outside of the machine when abnormality occurs in the machine or the process.	
Exhaust capacity	m ³ /min	4 or higher *at the exhaust duct hose connection port of the machine main body when static pressure is as below mentioned.
Static pressure	Pa	-1200 to -130 (at the exhaust duct hose connection port of the machine main body)
Utility unit exhaust system:	Function Detect gas leakage inside the utility unit and exhaust heat.	
Exhaust capacity	m ³ /min	7 or higher (at the exhaust duct hose connection port of the machine main body when static pressure is as below mentioned.)
Static pressure	Pa	-1200 ~ -100 (at the exhaust duct hose connection port of the machine main body)
Process gas exhaust system:	Function Exhaust gases after processing	
Exhaust capacity	m ³ /min	0.6 or higher * This system expels gases generated in the etching process after they pass through the gas filter. Unused SF ₆ is included in the gases.
Static pressure	Pa	-1,200 ~ -45 (at the exhaust duct hose connection port of the machine main body)
Machine Dimensions (W x D x H)	Main body 1,400 x 2,500 x 1,800 (excluding the status indicator (324 mm) and other protrusions)	
Utility unit	775 x 942 x 1,525	
Coolant unit (2)	413 x 610 x 664 (per unit) 540 x 743 x 772 (per unit)	
Machine Weight	Main body kg About 870	
Utility unit	kg About 230 (excluding the gas filter of about 40 kg)	
Coolant unit (2)	About 90 x 2 About 130 x 2	

Environmental conditions

- Use clean, oil-free air at a dew point of -15 °C or less. (Use a residual oil: 0.1 ppm. Filtration rating: 0.01 µm/99.5 % or more).
- Keep room temperature fluctuations within ±1 °C of the set value. (Set value should be between 20 ~ 25 °C).
- The machines should be used in an environment, free from external vibration. Do not install machine near a ventilation opening, heat generation equipment or oil mist generating parts.
- Be sure to use compressed air as the main air and sub air sources.
- Residual gas exhausted from the machine after etching contains such toxic substances as HF, SiF₄, SOF₂ and SF₆. Follow the environmental protection codes of the area the machine is installed for control/disposal of such substances.
- In case of water leakage, please install the machine on the floor with sufficient waterproofing and drainage treatments.
- Please install a gas leakage detector at the plant (at the customer side) as well.
- You must wear a gas mask when performing maintenance work. Make sure to have one ready.
- Please prepare emergency plans to deal with accidents.
- All pressures specified above are gauge pressures.
- As the above specification may change due to technical modifications, Please confirm when placing your order.
- For further information, please contact your local sales representative.



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